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Y. Robinson
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: PARIKH et al.

Serial No. 09/911,155

Group Art Unit: 2811

Filed: July 23, 2001

Title: GALLIUM NITRIDE BASED DIODES WITH LOW FORWARD VOLTAGE AND LOW REVERSE CURRENT OPERATION

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Sir:


This certification is being made for the Information Disclosure Statement accompanying this certification. Applicants submit a copy of each of the references listed on the attached supplemental PTO-1449 (Modified) form for consideration by the Examiner.

I, the person signing below certify that:

(a) each item of information contained in the information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of the information disclosure statement (37 C.F.R. § 1.97(e)(1)); or

(b) no item of information contained in the information disclosure statement, to the knowledge of the person signing the certification after making reasonable inquiry, was known to any individual designated in § 1.56(c) more than three months prior to the filing of the statement. 37 C.F.R. § 1.97(e)(2).

Respectfully submitted,

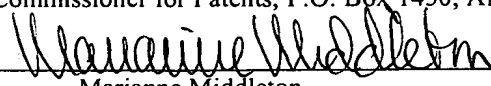

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CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on

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U.S. PATENT DOCUMENTS

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FOREIGN PATENT DOCUMENTS

[illegible]

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

	1	ZHANG A P et al, "COMPARISON OF GAN P-I-N AND SCHOTTKY RECTIFIER PERFORMANCE", IEEE TRANSACTIONS ON ELECTRON DEVICES, IEEE INC. NEW YORK, US, Vol. 48, No. 3, March 2001 (2001-03), p. 407-411, XP001038984 ISSN, 0018-9383
	2	MOHAMMAD S N et al. "NEAR-IDEAL PLATINUM-GaN SCHOTTKY DIODES", ELECTRONICS LETTERS, IEE STEVENAGE, GB, Vol. 32, No. 6, 3/14/96, p. 598-599, XP006004867, ISSN, 0013-5194.
	3	SCHMITZ A C A et al., "METAL CONTACTS TO N-TYPE GaN", III-V NITRIDES AND SILICON CARBIDE, FORT COLLINS, CO, USA, 1997, Vol. 27, No. 4, p. 255-260, XP008016192, JOURNAL OF ELECTRONIC MATERIALS, 4/1998, TMS, USA, ISSN, 0361-5235
Examiner	Date Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.